

自主封測 品質把控 售後保障

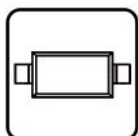
WEB | WWW.TDSEMIC.COM



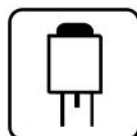
電源管理



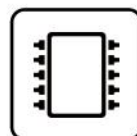
顯示驅動



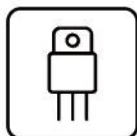
二三極管



LDO穩壓器



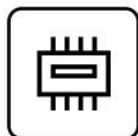
觸摸芯片



MOS管



運算放大器



存儲芯片



MCU



串口通信

1N5819W S4

產品規格說明書

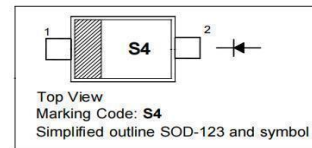
1N5819W S4

Features

- Low Forward Voltage

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	40 30 20	V
Reverse Voltage	V_R	40 30 20	V
Average Forward Rectified Current	$I_{F(AV)}$	350	mA
Non-Repetitive Peak Forward Surge Current at $t = 1$ s	I_{FSM}	2	A
Power Dissipation	P_{tot}	400	mW
Operating and Storage Temperature Range	T_j, T_{stg}	- 65 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 10 \mu\text{A}$	$V_{(BR)R}$	40 30 20	- - -	- - -	V
Reverse Leakage Current at $V_R = 30$ V at $V_R = 20$ V at $V_R = 10$ V	I_R	- - -	- - -	5 5 5	μA
Forward Voltage at $I_F = 20$ mA at $I_F = 200$ mA	V_F	- -	- -	0.37 0.6	V
Total Capacitance at $V_R = 0$ V, $f = 1$ MHz	C_T	-	50	-	pF
Reverse Recovery Time at $I_F = I_R = 200$ mA, $I_{rr} = 0.1 I_R$, $R_L = 100 \Omega$	t_{rr}	-	10	-	ns

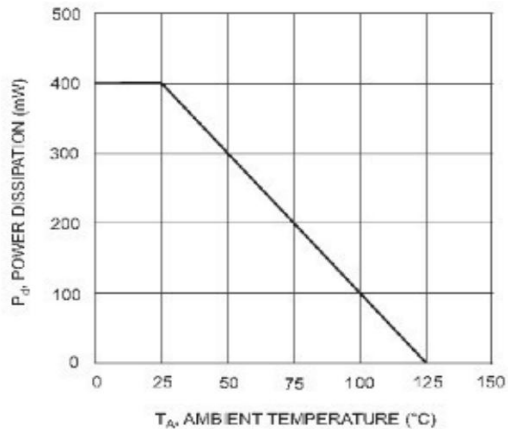


Fig. 1 Power Derating Curve

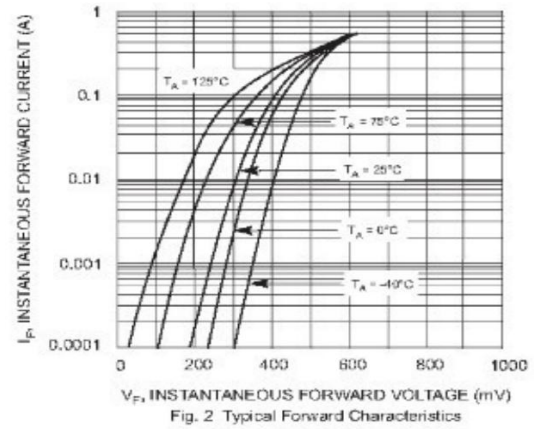


Fig. 2 Typical Forward Characteristics

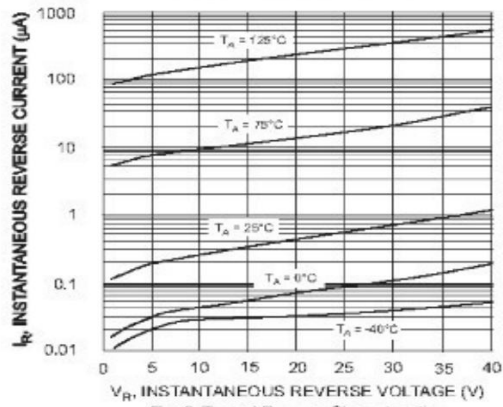


Fig. 3 Typical Reverse Characteristics

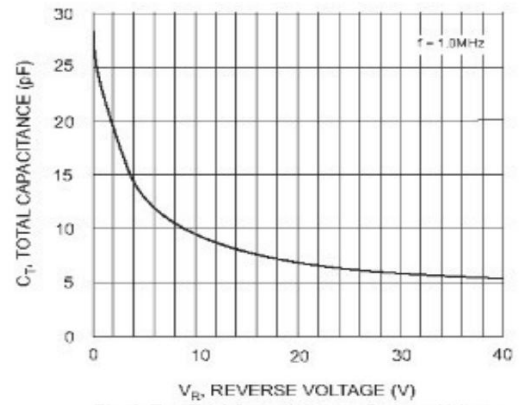


Fig. 4 Typ. Total Capacitance vs. Reverse Voltage

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-123

